

1 ABSTRACT OF THE DISCLOSURE

2       The invention includes a method of forming a capacitor structure.  
3       A first electrical node is formed, and a layer of metallic aluminum is  
4       formed over the first electrical node. Subsequently, an entirety of the  
5       metallic aluminum within the layer is transformed into one or more of  
6       AlN, AlON, and AlO, with the transformed layer being a dielectric  
7       material over the first electrical node. A second electrical node is then  
8       formed over the dielectric material. The first electrical node, second  
9       electrical node and dielectric material together define at least a portion  
10      of the capacitor structure. The invention also pertains to a capacitor  
11      structure which includes a first electrical node, a second electrical node,  
12      and a dielectric material between the first and second electrical nodes.  
13      The dielectric material consists essentially of aluminum, oxygen and  
14      nitrogen.

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